

ESDS312、ESDS314 数据线路浪涌和 ESD 保护二极管矩阵

1 特性

- IEC 61000-4-2 4 级静电放电 (ESD) 保护
 - $\pm 30\text{kV}$ 接触放电
 - $\pm 30\text{kV}$ 气隙放电
- IEC 61000-4-4 瞬态放电 (EFT) 保护
 - 80A (5/50ns)
- IEC 61000-4-5 浪涌保护
 - 25A (8/20 μs)
 - 低浪涌钳位电压在 25A I_{pp} 下为 6.5V
- IO 电容:
 - 4.5pF (典型值)
- 直流击穿电压: 5.5V (最小值)
- 超低泄漏电流: 5nA (典型值)
- 支持速率高达 5Gbps 的高速接口
- 工业温度范围: -40°C 至 $+125^{\circ}\text{C}$
- 简易直通布线封装 (ESDS312)

2 应用

- 终端设备
 - 以太网交换机
 - 接入点
 - 网关
 - 打印机
 - 数字视频录像机 (DVR) 和网络视频录像机 (NVR)
- 接口
 - 以太网 10/100/1000Mbps
 - USB 2.0
 - 通用输入/输出 (GPIO)

3 说明

ESDS314、ESDS312 是一种单向 TVS ESD 保护二极管阵列，用于高达 25A (8/20 μs) 的以太网、USB 和通用数据线路浪涌保护。ESDS314、ESDS312 器件的额定 ESD 冲击消散值达到了 IEC 61000-4-2 (4 级) 国际标准中规定的最高水平。

这些器件 每通道 具有 4.5pF IO 电容，因此非常适合用于保护高速接口，如以太网 10/100/1000、USB 2.0 和 GPIO。低动态电阻和低钳位电压确保系统级抗瞬变事件保护。

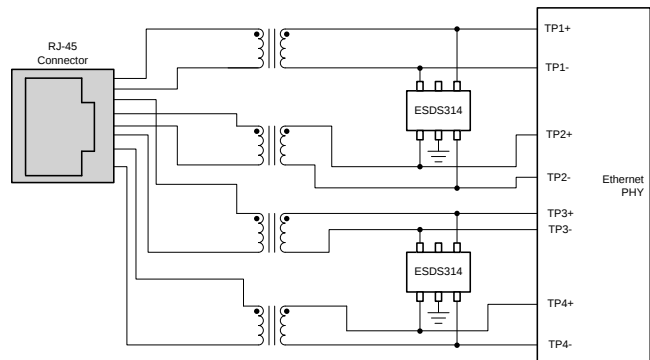
ESDS314、ESDS312 器件采用符合行业标准的 5 引脚 SOT23 封装。

器件信息⁽¹⁾

器件编号	封装	封装尺寸 (标称值)
ESDS314	SOT23 (5)	2.9mm x 1.6mm x 1.25mm
ESDS312	SOT23 (5); 2 NC 引脚	2.9mm x 1.6mm x 1.25mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

典型应用原理图



目录

1	特性	1	7.3	Feature Description	8
2	应用	1	7.4	Device Functional Modes	8
3	说明	1	8	Application and Implementation	9
4	修订历史记录	2	8.1	Application Information	9
5	Pin Configuration and Functions	3	8.2	Typical Application	9
6	Specifications	4	9	Power Supply Recommendations	11
6.1	Absolute Maximum Ratings	4	10	Layout	11
6.2	ESD Ratings -JEDEC Specifications	4	10.1	Layout Guidelines	11
6.3	ESD Ratings - IEC Specifications	4	10.2	Layout Example	11
6.4	Recommended Operating Conditions	4	11	器件和文档支持	12
6.5	Thermal Information	4	11.1	接收文档更新通知	12
6.6	Electrical Characteristics	5	11.2	社区资源	12
6.7	Typical Characteristics	6	11.3	商标	12
7	Detailed Description	8	11.4	静电放电警告	12
7.1	Overview	8	11.5	术语表	12
7.2	Functional Block Diagram	8	12	机械、封装和可订购信息	12

4 修订历史记录

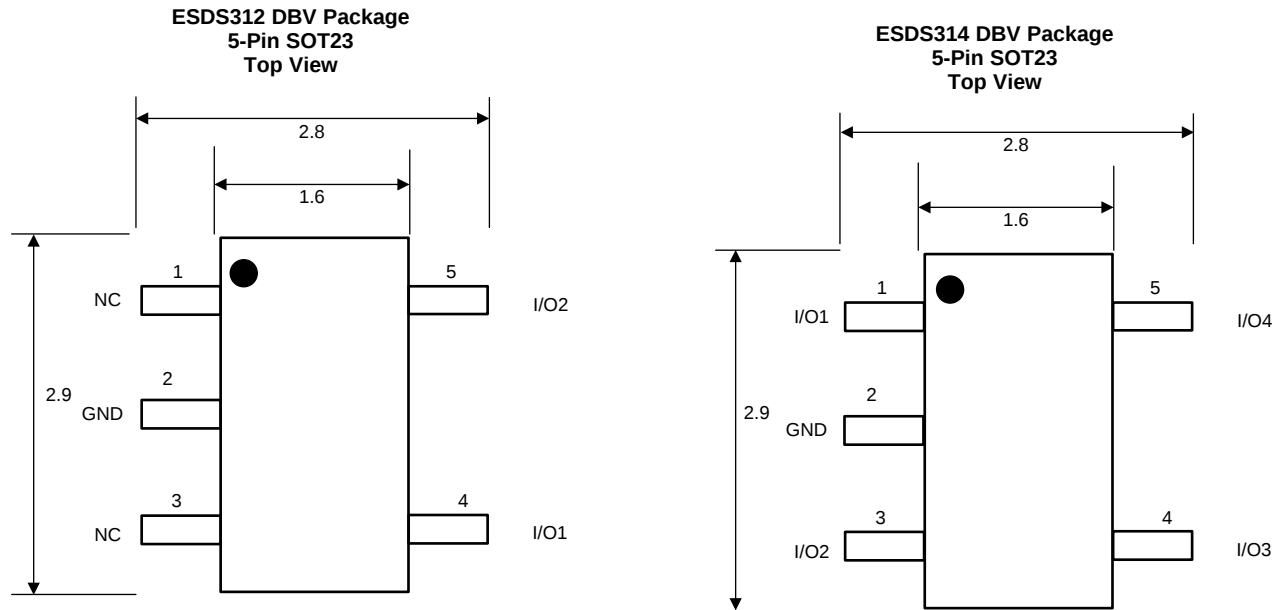
Changes from Revision A (July 2018) to Revision B Page

• 已更改 将“预告信息”更改成了“生产数据”	1
-------------------------------	----------

Changes from Original (May 2018) to Revision A Page

• 已更改 将“产品预览”更改成了“预告信息”	1
-------------------------------	----------

5 Pin Configuration and Functions



Pin Functions for ESDS312

PIN		TYPE	DESCRIPTION
NAME	NO.		
I/O1	4	I/O	Surge/ESD protected channels. Connect to the lines being protected.
I/O2	5		
GND	2	GND	Ground. Connect to ground.
NC	1	NC	Not connected; Used for optional straight-through routing. Can be left floating or grounded
NC	3		

Pin Functions for ESDS314

PIN		TYPE	DESCRIPTION
Name	No.		
I/O1	1	I/O	Surge/ESD protected channels. Connect to the lines being protected.
I/O2	3		
I/O3	4		
I/O4	5		
GND	2	GND	Ground. Connect to ground

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
IEC 61000-4-4 Electrical Fast Transient	Peak Power at 25 °C		80	A
IEC 61000-4-5 Surge (t _p 8/20 μs)	Peak Power at 25 °C		170	W
	Peak Current at 25 °C		25	A
T _A	Operating free-air temperature	–40	125	°C
T _{stg}	Storage temperature	–65	155	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings -JEDEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. [Following sentence optional; see the wiki.] Manufacturing with less than 500-V HBM is possible with the necessary precautions. [Following sentence optional; see the wiki.] Pins listed as ±WWW V and/or ±XXX V may actually have higher performance.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. [Following sentence optional; see the wiki.] Manufacturing with less than 250-V CDM is possible with the necessary precautions. [Following sentence optional; see the wiki.] Pins listed as ±YYY V and/or ±ZZZ V may actually have higher performance.

6.3 ESD Ratings - IEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	IEC 61000-4-2 Contact Discharge, all pins	±30000	V
		IEC 61000-4-2 Air Discharge, all pins	±30000	

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	Input voltage	0		3.6	V
T _A	Operating Free Air Temperature	–40		125	°C

6.5 Thermal Information

THERMAL METRIC ⁽¹⁾		ESDS312	ESDS314	UNIT
		DBV (SOT-23)	DBV (SOT-23)	
		5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	163.9	127.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	113.4	78.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	76.9	43.9	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	59.8	24.5	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	76.8	43.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.6 Electrical Characteristics

At TA = 25°C unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{RWM}	Reverse stand-off voltage	I _{IO} < 500 nA, across operating temperature range			3.6	V
I _{LEAKAGE}	Leakage current at 3.6 V	V _{IO} = 3.6 V, Any IO pin to GND		5	50	nA
V _{BRF}	Breakdown voltage, IO to GND ⁽¹⁾	I _{IO} = 1 mA	4.5		7.5	V
V _{FWD}	Forward Voltage, GND to IO	I _{IO} = 1 mA		0.8		V
V _{HOLD}	Holding Voltage, IO to GND ⁽²⁾	I _{IO} = 1 mA		5		V
V _{CLAMP}	Surge Clamping voltage, t _p = 8/20 μs	I _{PP} = 1 A, Any IO pin to GND		5		V
V _{CLAMP}		I _{PP} = 12 A, Any IO pin to GND		5.6		V
V _{CLAMP}		I _{PP} = 25 A, Any IO pin to GND		6.5		V
V _{CLAMP}		I _{PP} = 1 A, GND to any IO pin		1		V
V _{CLAMP}		I _{PP} = 12 A, GND to any IO pin		2.1		V
V _{CLAMP}		I _{PP} = 25 A, GND to any IO pin		3.6		V
V _{CLAMP}	TLP Clamping Voltage, t _p = 100 ns	I _{PP} = 16 A, Any IO pin to GND		5.5		V
V _{CLAMP}		I _{PP} = 16 A, GND to any IO pin		2.2		V
C _{LINE}	Line capacitance, Any IO to GND	V _{IO} = 0 V, V _{p-p} = 30 mV, f = 1 MHz		4.5	5.5	pF
ΔC _{LINE}	Variation of line capacitance	C _{LINE1} - C _{LINE2} , V _{IO} = 0 V, V _{p-p} = 30 mV, f = 1 MHz		0.05	0.1	pF
C _{CROSS}	Line-to-line capacitance	V _{IO} = 0V, V _{rms} = 30 mV, f = 1 MHz		2.25	2.75	pF

(1) V_{BRF} and V_{BRR} are defined as the voltage obtained at 1 mA when sweeping the voltage up, before the device latches into the snapback state

(2) V_{HOLD} is defined as the voltage when 1 mA is applied, after the device has successfully latched into the snapback state.

6.7 Typical Characteristics

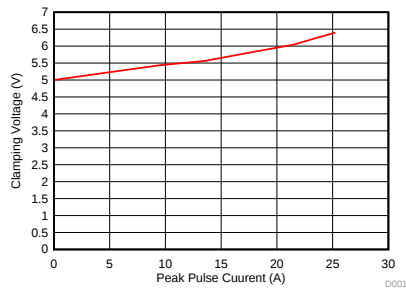


图 1. Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$), Any IO Pin to GND

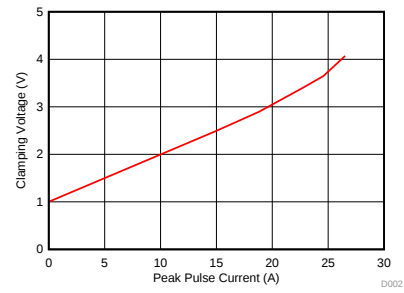


图 2. Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$), GND to Any IO Pin

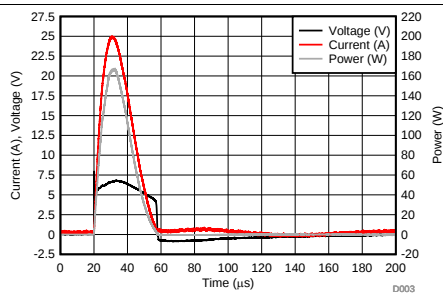


图 3. Surge Current, Clamping Voltage and Power Curve ($t_p = 8/20 \mu s$), Any IO Pin to GND

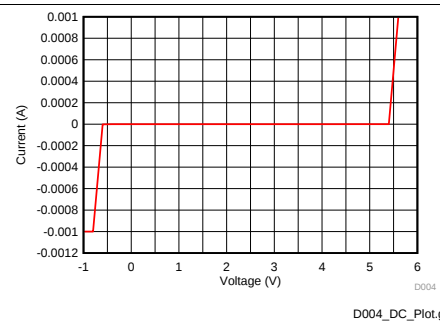


图 4. DC I-V Curve



图 5. TLP I-V Curve, IO to GND, $t_p = 100 \text{ ns}$

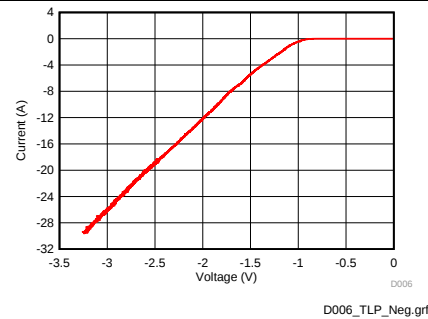


图 6. TLP I-V Curve, IO to GND Negative, $t_p = 100 \text{ ns}$

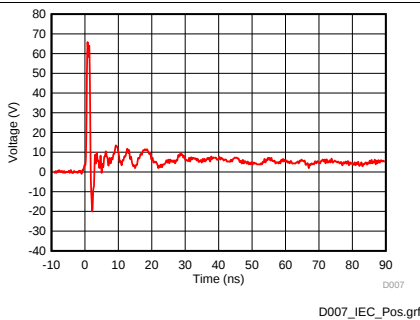


图 7. +8 kV IEC 61000-4-2 Clamping Voltage Waveform

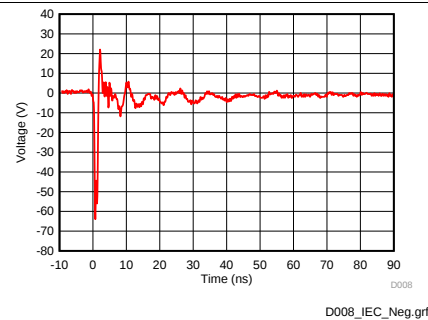


图 8. -8 kV IEC 61000-4-2 Clamping Voltage Waveform

Typical Characteristics (接下页)

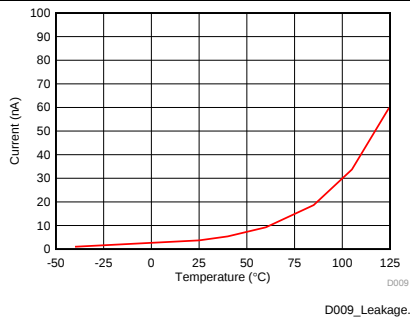


图 9. DC Leakage vs. Ambient Temperature, Bias Voltage = 3.6 V

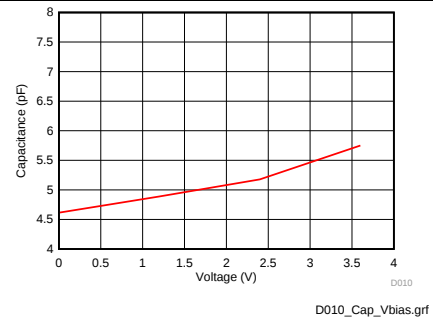


图 10. Capacitance vs. Bias Voltage at 25°C

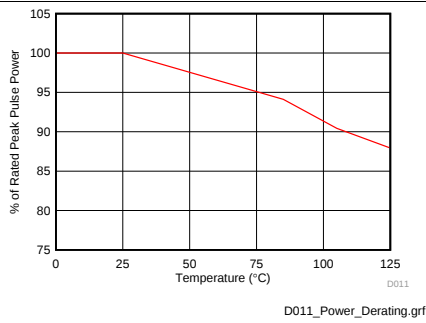


图 11. Surge Power Derating with Respect To Ambient Temperature

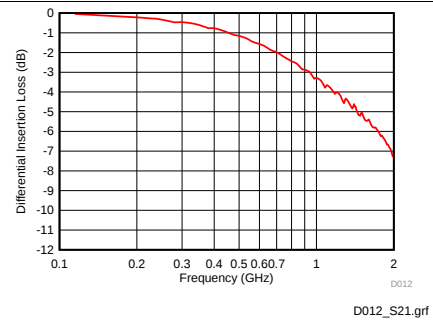


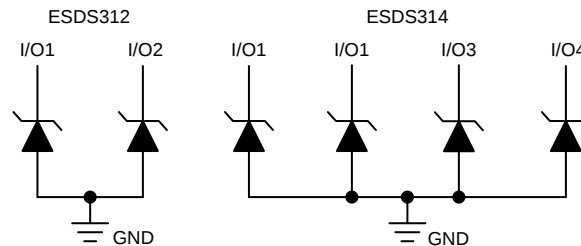
图 12. Differential Insertion Loss

7 Detailed Description

7.1 Overview

The ESDS314, ESDS312 devices are unidirectional ESD Protection Diode with a low capacitance. These devices can dissipate high surge currents upto 25 A (8/20 μ s) and ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The low capacitance makes this device ideal for protecting high-speed signal interfaces such as Ethernet 10/100/1000 Mbps and general purpose high speed data lines.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 IEC 61000-4-4 EFT Protection

The I/O pins of ESDS314 and ESDS312 can withstand surge events (IEC 61000-4-5, 8/20 μ s waveform) up to 25 A and 170 W. These devices also provide ESD protection up to ± 30 -kV contact and ± 30 -kV air gap per IEC 61000-4-2 standard. The I/O pins can withstand an electrical fast transient burst of up to 80 A (IEC 61000-4-4 5/50 ns waveform, 4 kV with 50- Ω impedance). The capacitance between each I/O pin to ground is 4.5 pF (typical) and 5.5 pF (maximum). This device supports data rates up to 1 Gbps.

The reverse DC breakdown voltage of each I/O pin is a minimum of 4.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 3.6 V. The I/O pins feature an ultra-low leakage current of 100 nA (maximum) with a bias of 3.6 V. This device features an industrial operating range of -40°C to $+125^{\circ}\text{C}$.

7.4 Device Functional Modes

The ESDS314, ESDS312 devices are a passive integrated circuit that triggers when voltages are above V_{BRF} or below 0.7 V. During ESD events, voltages as high as ± 30 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of ESDS314, ESDS312 (usually within a few nano-seconds) the devices reverts to passive.

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The ESDS314, ESDS312 devices are diode type TVS which is used to provide a path to ground for dissipating surge and ESD events on high-speed signal lines between a human interface connector and a system. As the current from surge or ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP} , to a safe level for the protected IC.

8.2 Typical Application

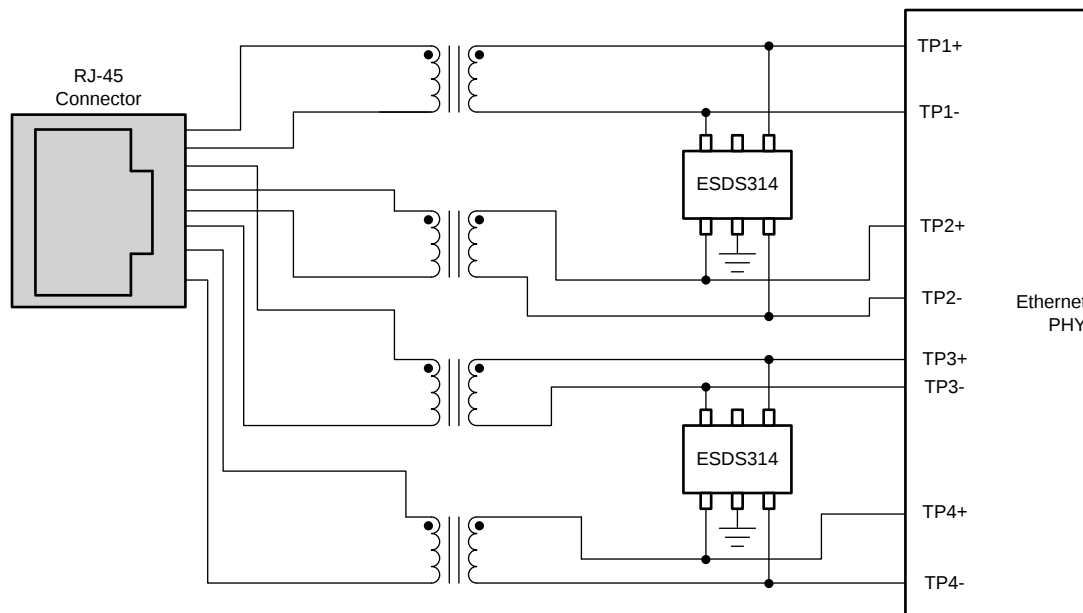


图 13. ESDS314 Protecting the Ethernet 1Gbps Interface

8.2.1 Design Requirements

A typical operation for the ESDS314 would be protecting a high speed dataline similar to one shown in 图 13. In this example, the ESDS314 is protecting an Ethernet PHY's data lines that has a nominal operating voltage of 3.6 V. Many of the Ethernet interfaces that connect to long cables require protection against ± 1 kV surge test through a $42\text{-}\Omega$ coupling resistor and a $0.5\text{ }\mu\text{F}$ capacitor, equaling roughly 24 A of surge current. Without any input protection, if a surge event is caused by lightning, coupling, ringing, or any other fault condition, this input voltage will rise to hundreds of volts for multiple microseconds, harming the device.

For Ethernet 1000Base-T (1Gbps), application design parameters listed in 表 1 are known.

表 1. Design Parameters

DESIGN PARAMETER	VALUE
Signal range on differential data line pairs	0 to 3.6 V
Operating frequency	125 MHz

8.2.2 Detailed Design Procedure

8.2.2.1 Signal Range

The ESDS314 has 4 identical surge protection channels with each channel supporting a signal range of 0 to 3.6 V. The device will work well with any Ethernet PHY that drives the single ended voltage on the data line up to a 3.6 V.

8.2.2.2 Operating Frequency

The ESDS314 has a capacitance of 4.5 pF (typical) and can support the 125 MHz operation of Ethernet 1000Base-T application

8.2.3 Application Curves

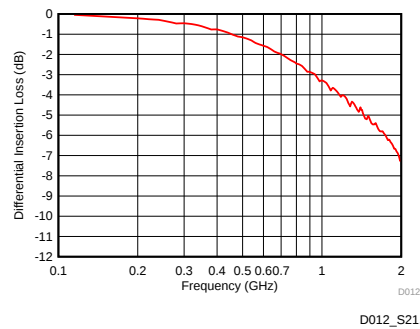


图 14. Differential Insertion Loss vs. Frequency

9 Power Supply Recommendations

The ESDS314, ESDS312 devices are passive ESD devices and there is no need to power it. Take care not to violate the recommended I/O specification (0 V to 3.6 V) to ensure the device functions properly.

10 Layout

10.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
 - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
 - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
 - Electric fields tend to build up on corners, increasing EMI coupling.

10.2 Layout Example

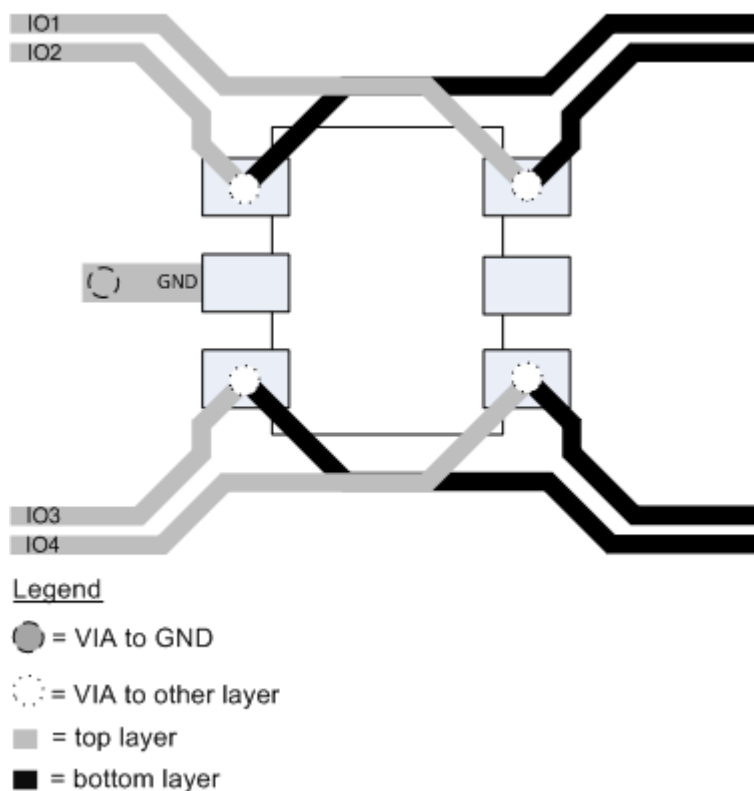


图 15. Layout Example for 4-channel Device

11 器件和文档支持

11.1 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的 [通知我](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

TI E2E™ 在线社区 [TI 的工程师对工程师 \(E2E\) 社区](#)。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 [TI 参考设计支持](#) 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

11.3 商标

E2E is a trademark of Texas Instruments.

11.4 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.5 术语表

SLYZ022 — [TI 术语表](#)。

这份术语表列出并解释术语、缩写和定义。

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

重要声明和免责声明

TI 均以“原样”提供技术性 & 可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用 TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的 TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及 TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它 TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对 TI 及其代表造成的损害。

TI 所提供产品均受 TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及 [ti.com.cn](http://www.ti.com.cn) 上或随附 TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改 TI 针对 TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2018 德州仪器半导体技术（上海）有限公司

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ESDS312DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1R4B	Samples
ESDS314DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1R2B	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ESDS312DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
ESDS314DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ESDS312DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
ESDS314DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0

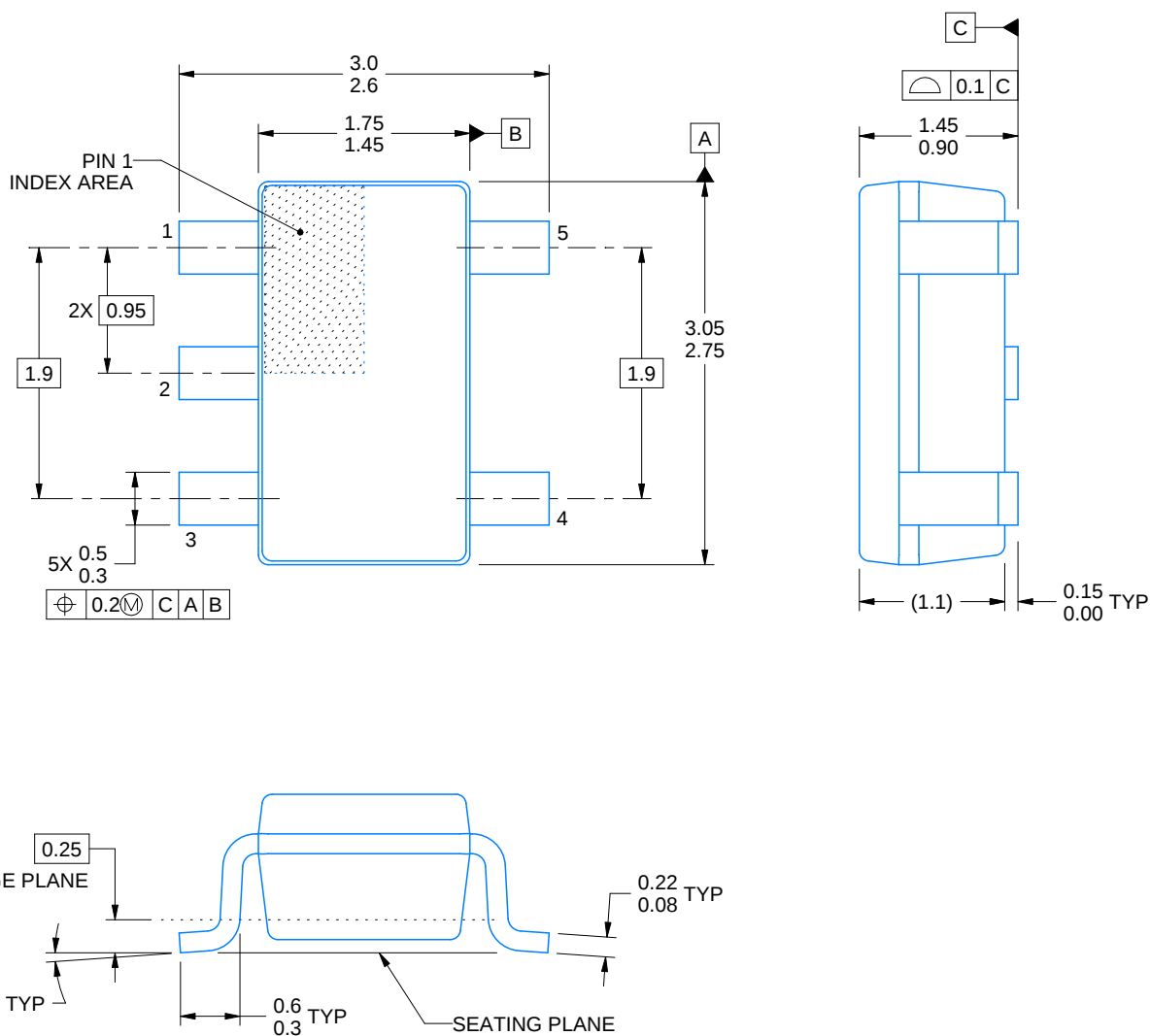


DBV0005A

PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214839/E 09/2019

NOTES:

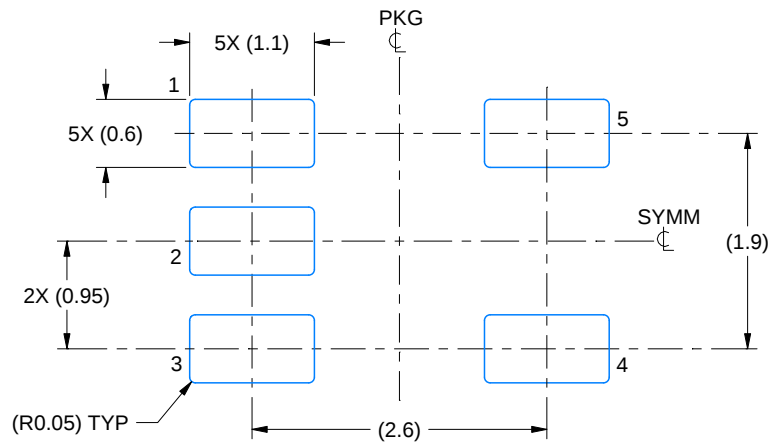
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

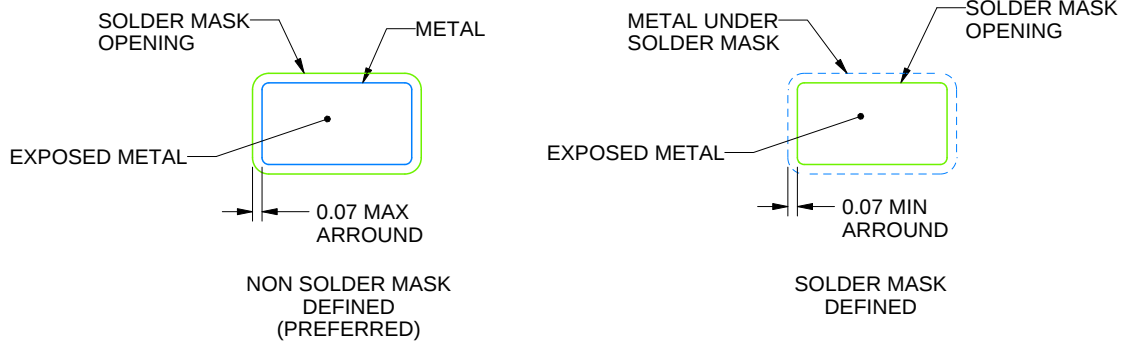
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/E 09/2019

NOTES: (continued)

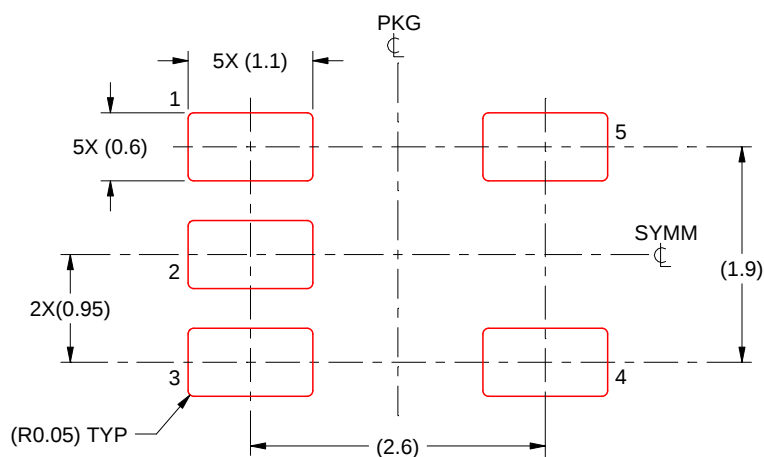
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/E 09/2019

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

TI 均以“原样”提供技术性 & 可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用 TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的 TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及 TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它 TI 或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI 对此概不负责，并且您须赔偿由此对 TI 及其代表造成的损害。

TI 所提供产品均受 TI 的销售条款 (<http://www.ti.com.cn/zh-cn/legal/termsofsale.html>) 以及 [ti.com.cn](http://www.ti.com.cn) 上或随附 TI 产品提供的其他可适用条款的约束。TI 提供所述资源并不扩展或以其他方式更改 TI 针对 TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2020 德州仪器半导体技术（上海）有限公司